# DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1996 1996 Sep 18



#### **Product specification**

### General purpose diode

## BAX18

### FEATURES

- Hermetically sealed leaded glass SOD27 (DO-35) package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 2 A.

### APPLICATIONS

Rectifier applications.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

DESCRIPTION

 $(\bigcirc)$ 

The diode is type branded.

package.

The BAX18 is a general purpose diode fabricated in planar technology, and

Fig.1 Simplified outline (SOD27; DO-35) and symbol.

а

-

MAM246

encapsulated in the hermetically sealed leaded glass SOD27 (DO-35)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage		_	75	V
V <sub>R</sub>	continuous reverse voltage		_	75	V
I <sub>F</sub>	continuous forward current	see Fig.2; note 1	_	500	mA
I <sub>FRM</sub>	repetitive peak forward current		_	2000	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	55	А
		t = 100 μs	_	15	А
		t = 10 ms	_	9	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	450	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

#### Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

BAX18

### ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 300 mA	_	1.0	V
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 150 °C	-	1.5	V
I <sub>R</sub>	reverse current	see Fig.5			
		V <sub>R</sub> = 75 V	-	5	μA
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	-	100	μA
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0; see Fig.6$	-	35	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$ ; measured at $I_R = 3$ mA; see Fig.7	_	50	ns

### THERMAL CHARACTERISTICS

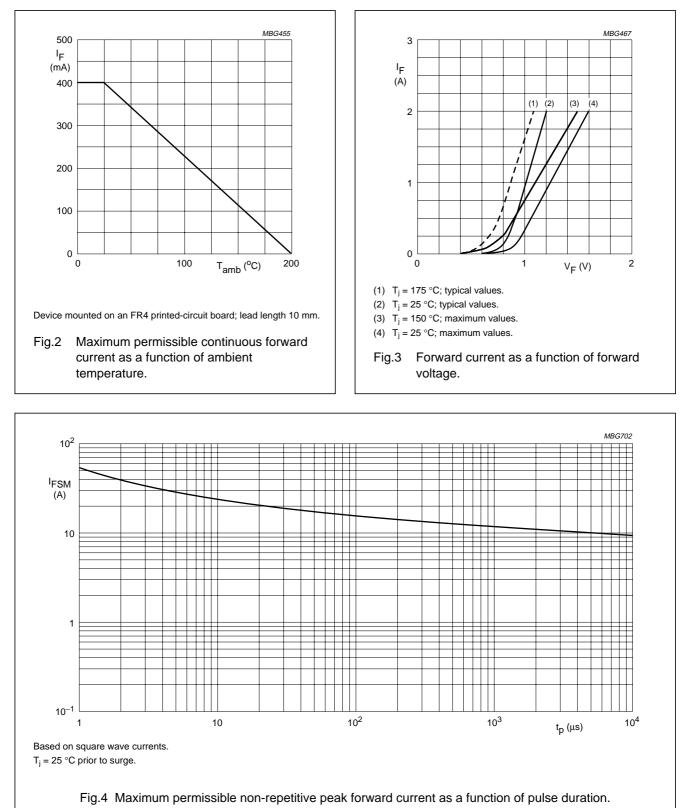
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length 10 mm; note 1	375	K/W

Note

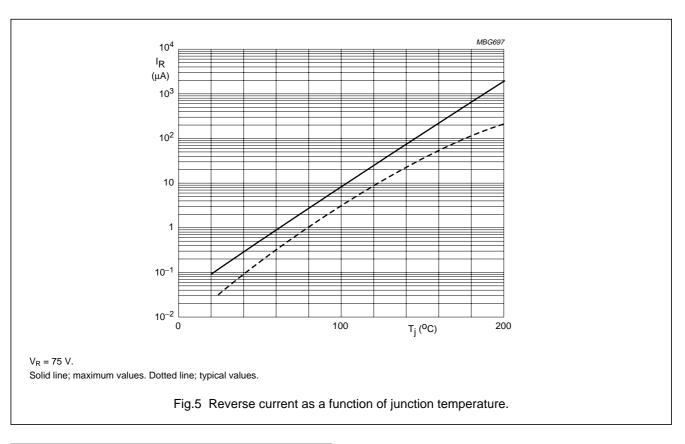
1. Device mounted on a printed circuit-board without metallization pad.

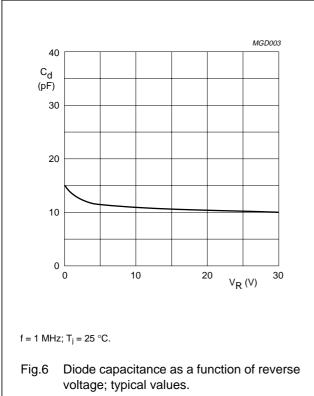
## BAX18

### **GRAPHICAL DATA**

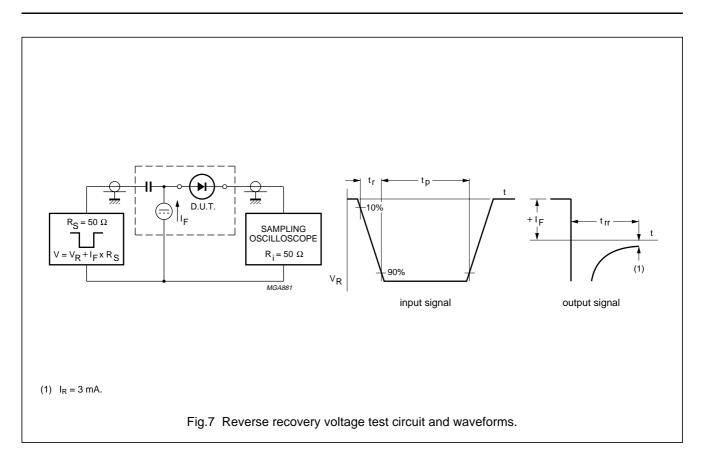


BAX18



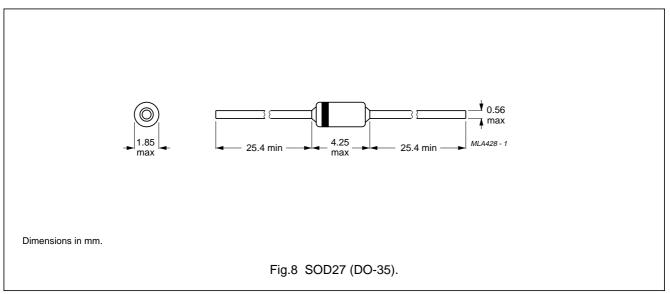


## BAX18



## BAX18

#### PACKAGE OUTLINE



#### DEFINITIONS

Data Sheet Status			
Objective specification	bjective specification This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.			
Application information			
Where application information is given, it is advisory and does not form part of the specification.			

### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.